

Controlling thermal boundary conductance with structure: From single interfaces to superlattices

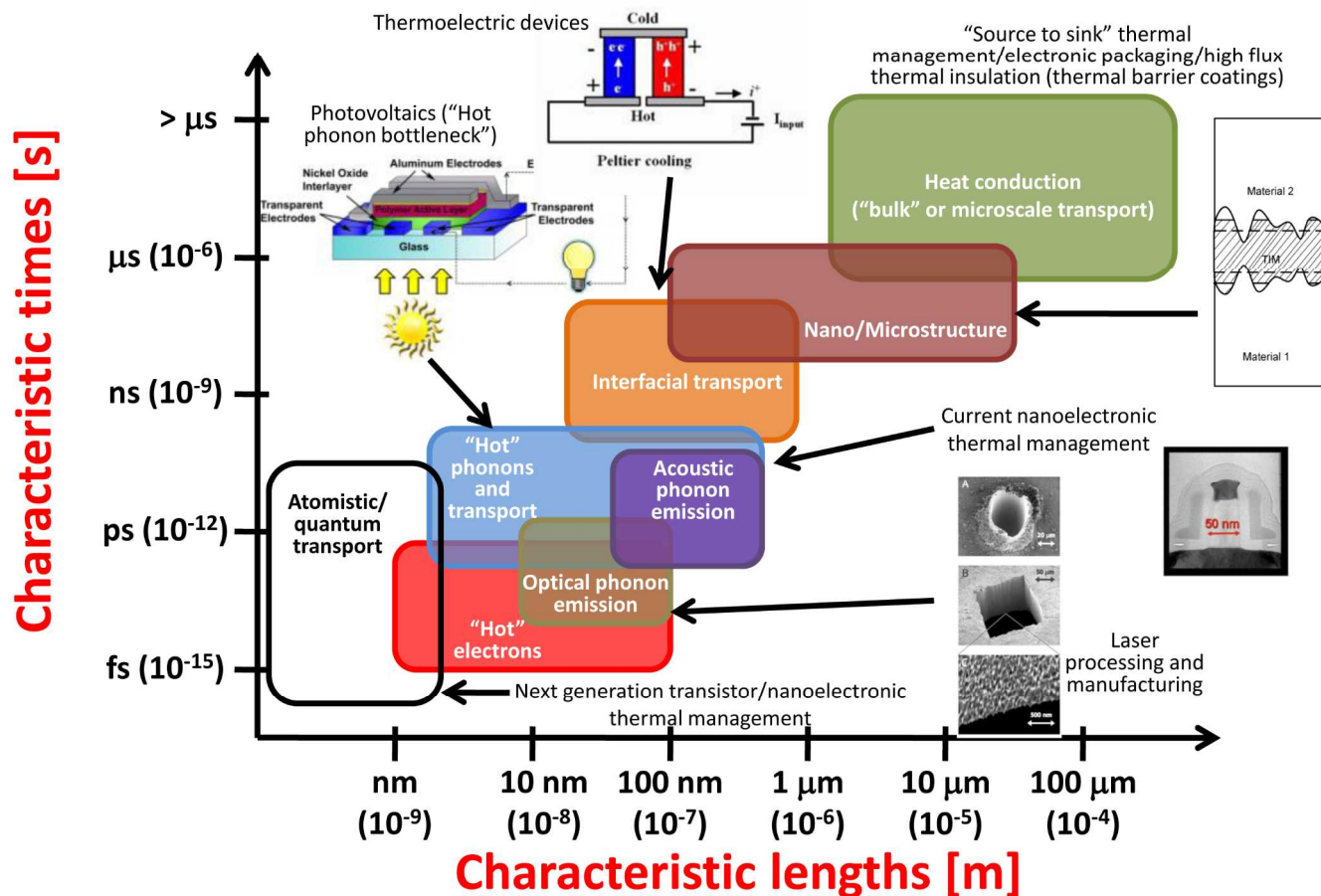
Patrick E. Hopkins

**Microscale Sciences and Technology Department
Sandia National Laboratories
Harry S. Truman Fellowship Program**

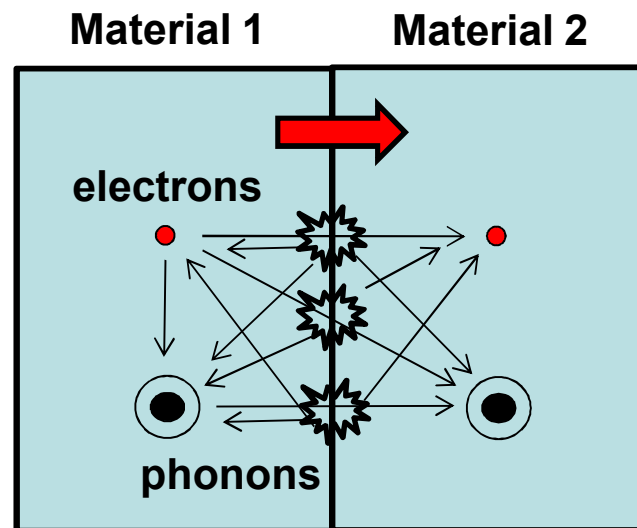
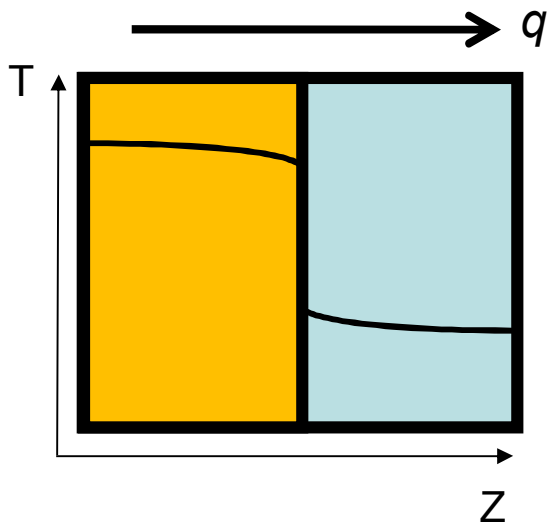
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Thermal transport regimes

Need to understand the “bottom” to engineer “up”

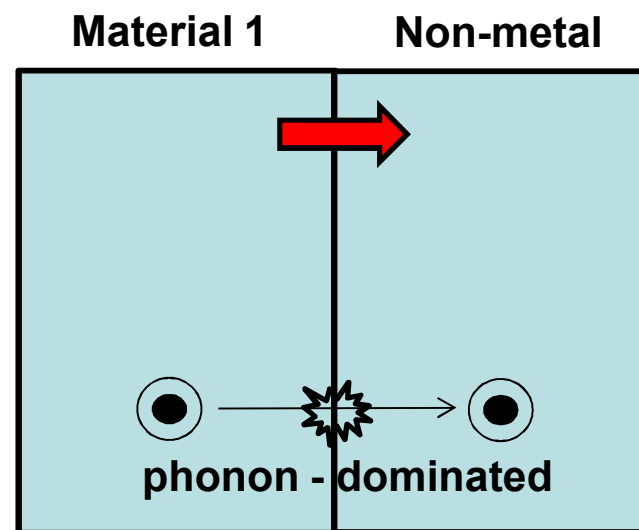
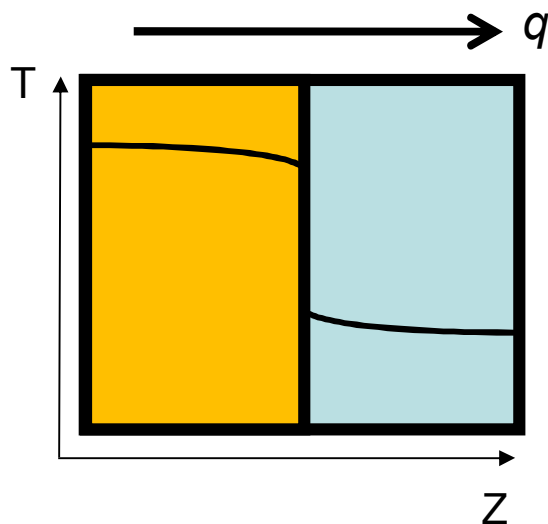


Thermal boundary conductance



$$q = h_K \Delta T = \frac{1}{R_K} \Delta T$$

Thermal boundary conductance



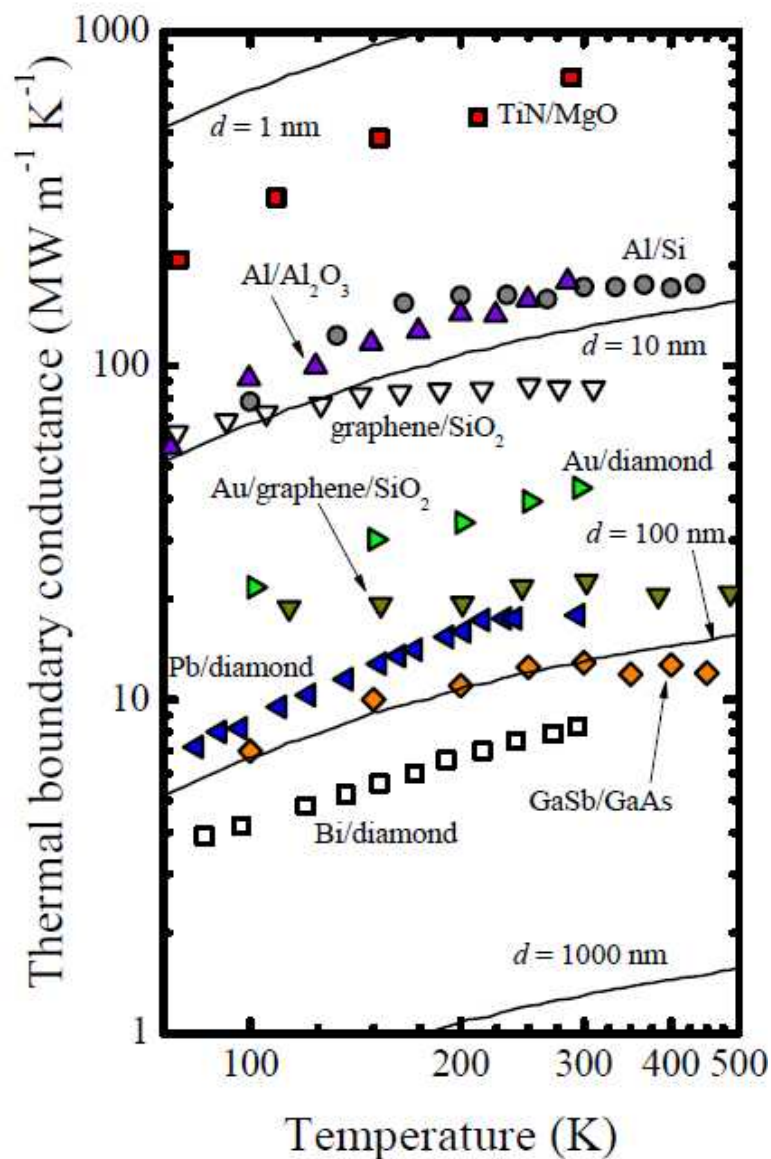
$$q = h_K \Delta T = \frac{1}{R_K} \Delta T$$



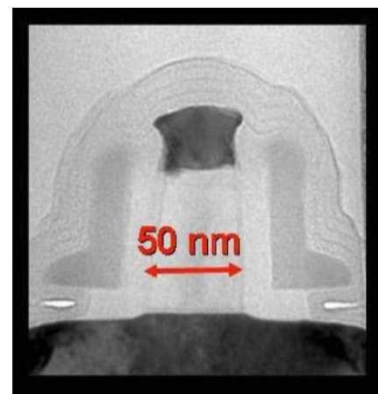
Outline

- **Thermal boundary conductance: background**
- **Time domain thermoreflectance (TDTR)**
- **Controlling h_K with structure and quantum dots**
 - **Collaborators: John Duda, Chris Petz, Jerry Floro (U. Virginia)**
- **Work in progress: Thermal transport in STO/CTO superlattices with structurally variant interfaces**
 - **Collaborators: Jayakanth, Pim, Ramesh, Arun (this group – Berkeley)**

Thermal boundary conductance



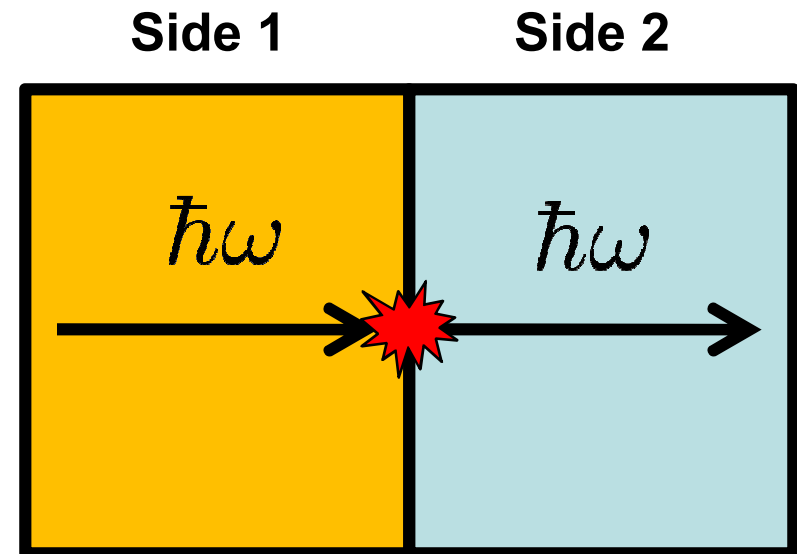
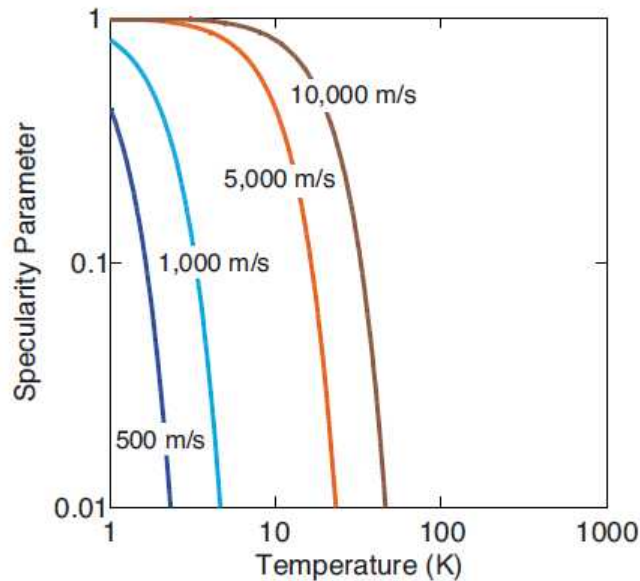
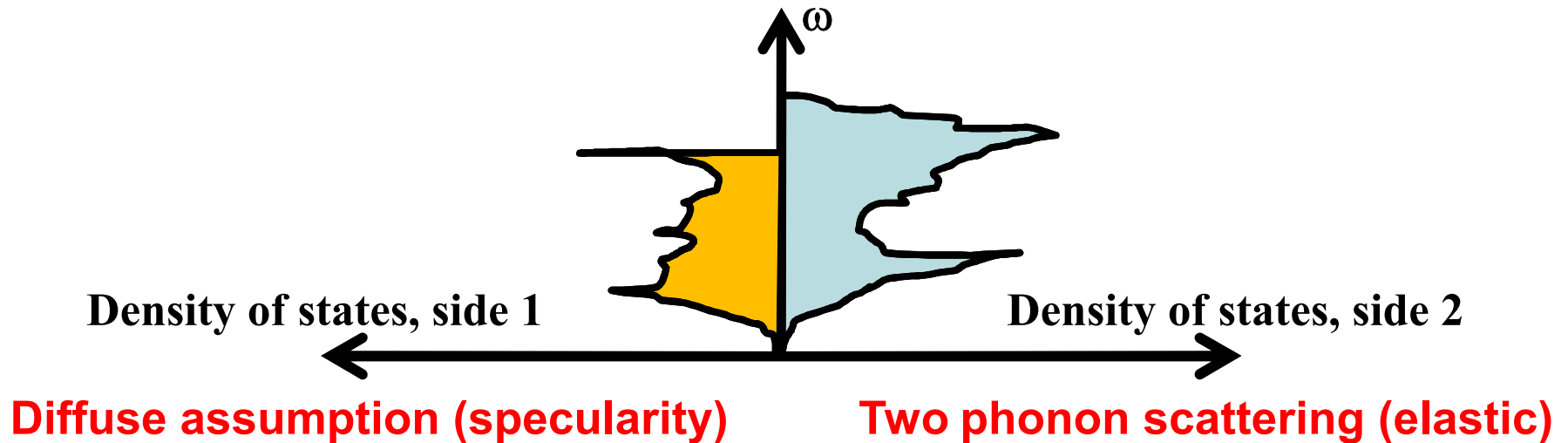
Nanoelectronic design



Thermoelectric nanomaterials

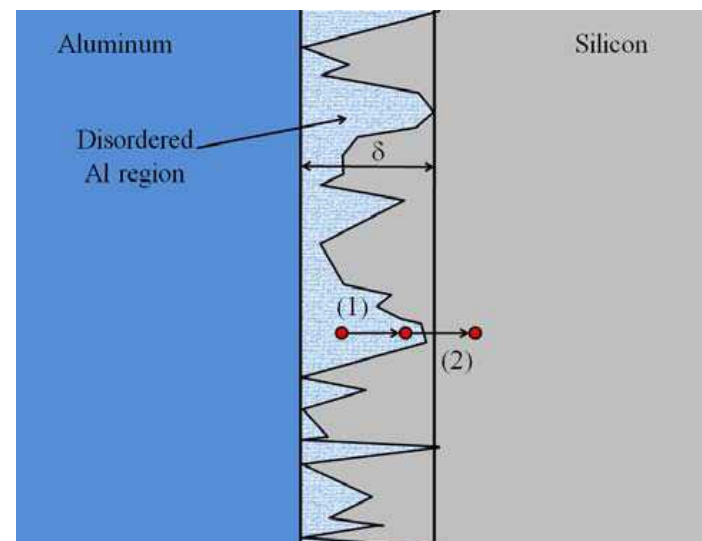
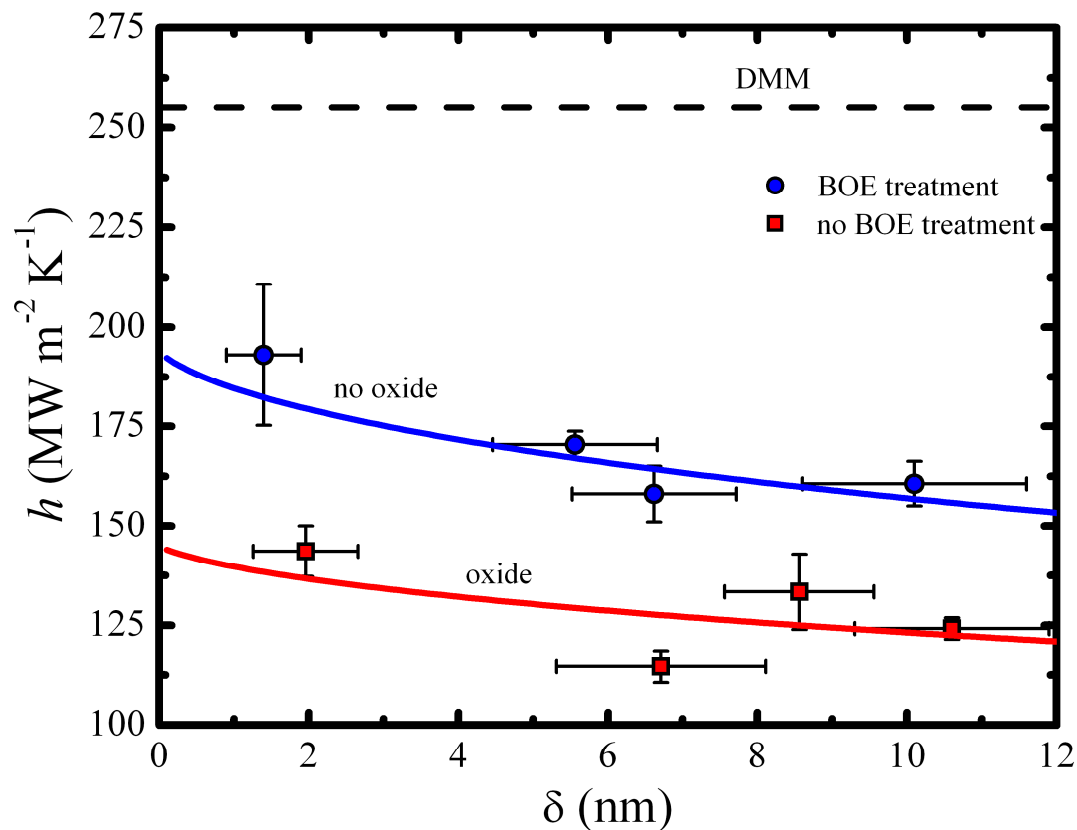
$$ZT = \frac{S^2 \sigma T}{\kappa}$$

Diffuse mismatch model (DMM)



Hopkins, *J. Appl. Phys.* 106, 013528 (2009)

Chemically roughened Al/Si interfaces



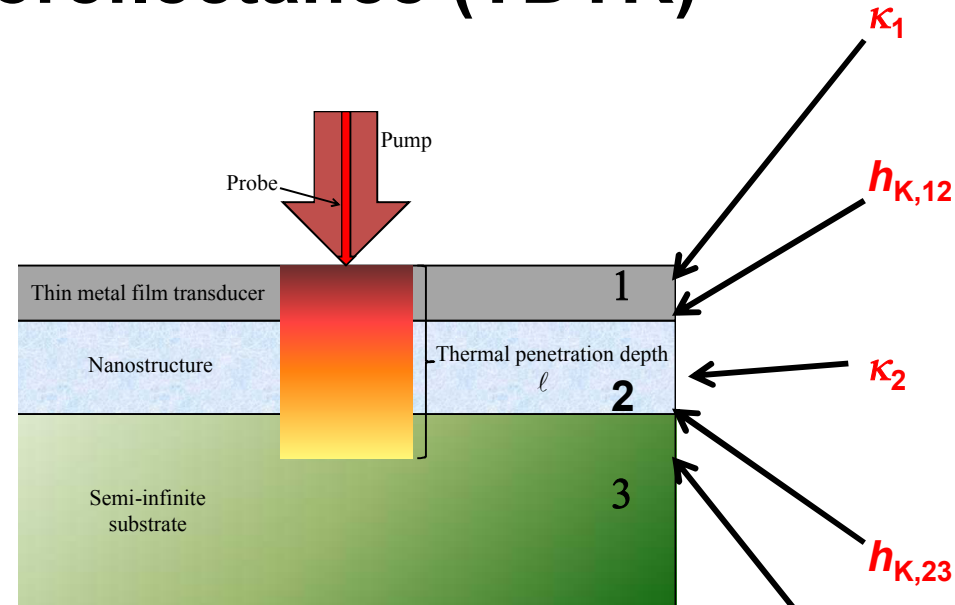
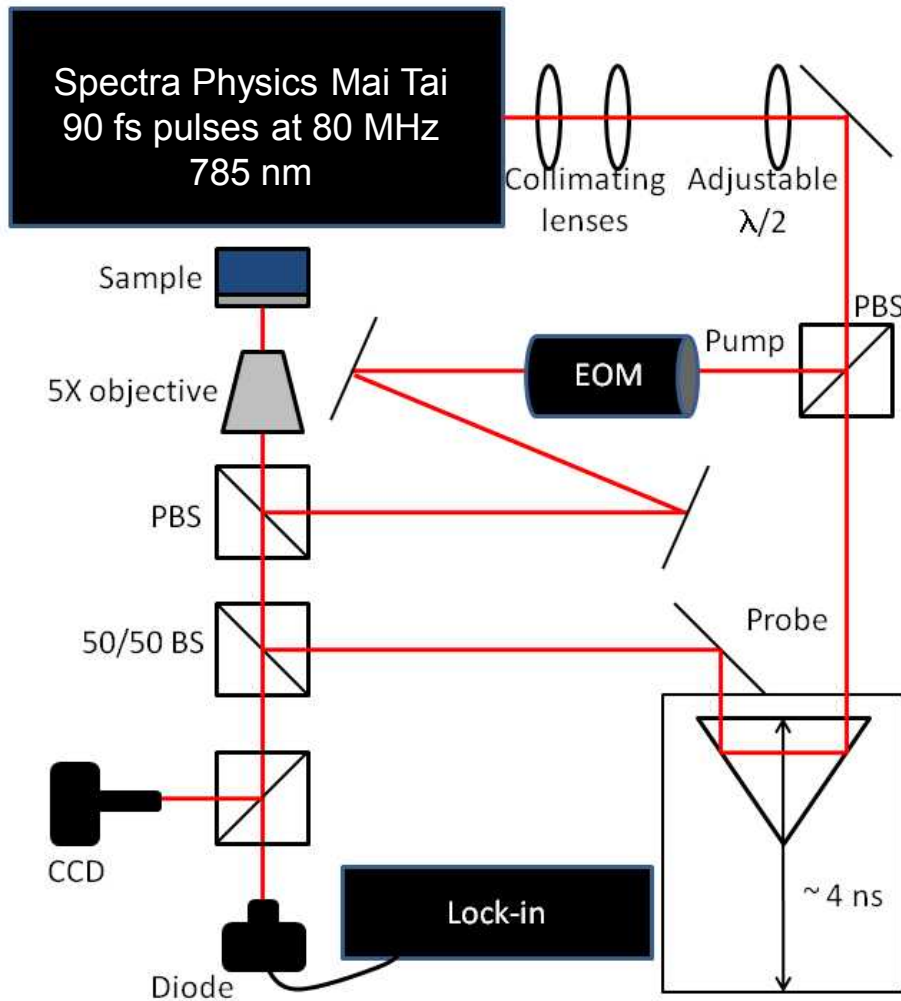
Hopkins *et al.*, *Phys. Rev. B* 82, 085307 (2010)



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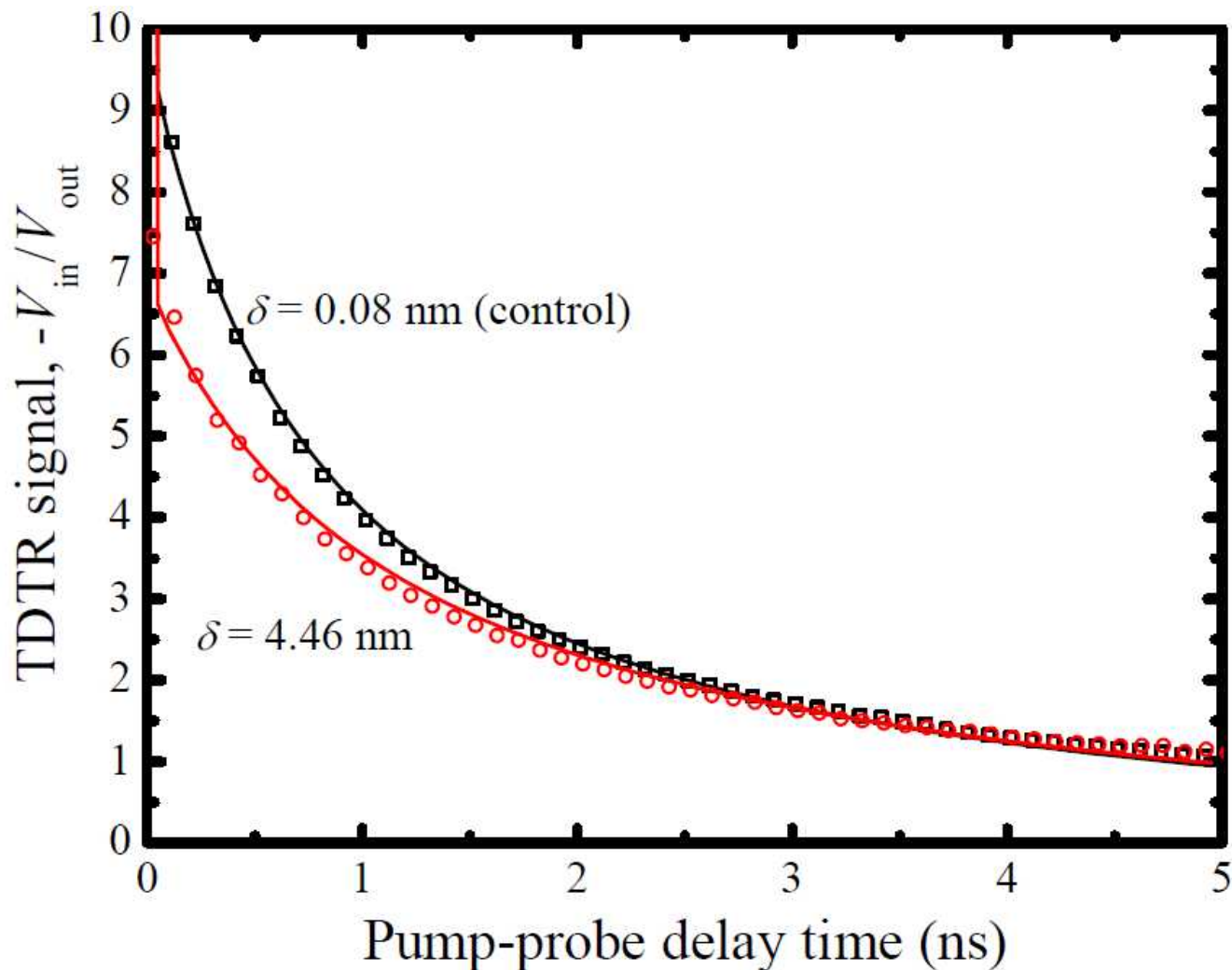
Time domain thermoreflectance (TDTR)



- Can measure thermal conductivity of thin films and substrates (κ) separately from thermal boundary conductance (h_{κ})
- Nanometer spatial resolution (~ 10 's of nm)
- Femtosecond to nanosecond temporal resolution
- Noncontact

Hopkins, *et al.*, *J. Heat Trans.* 132, 081302 (2010)

Time domain thermoreflectance (TDTR)

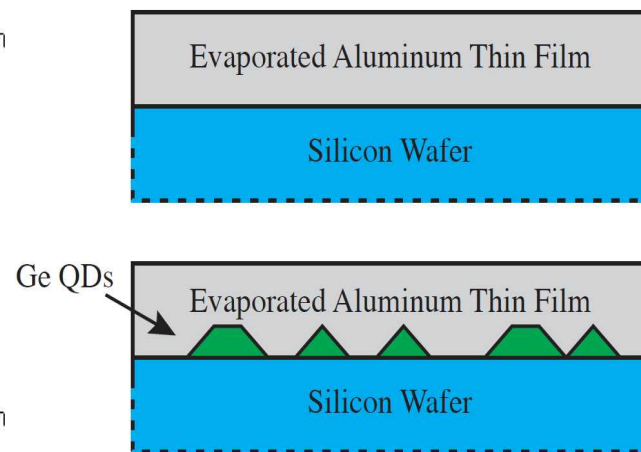
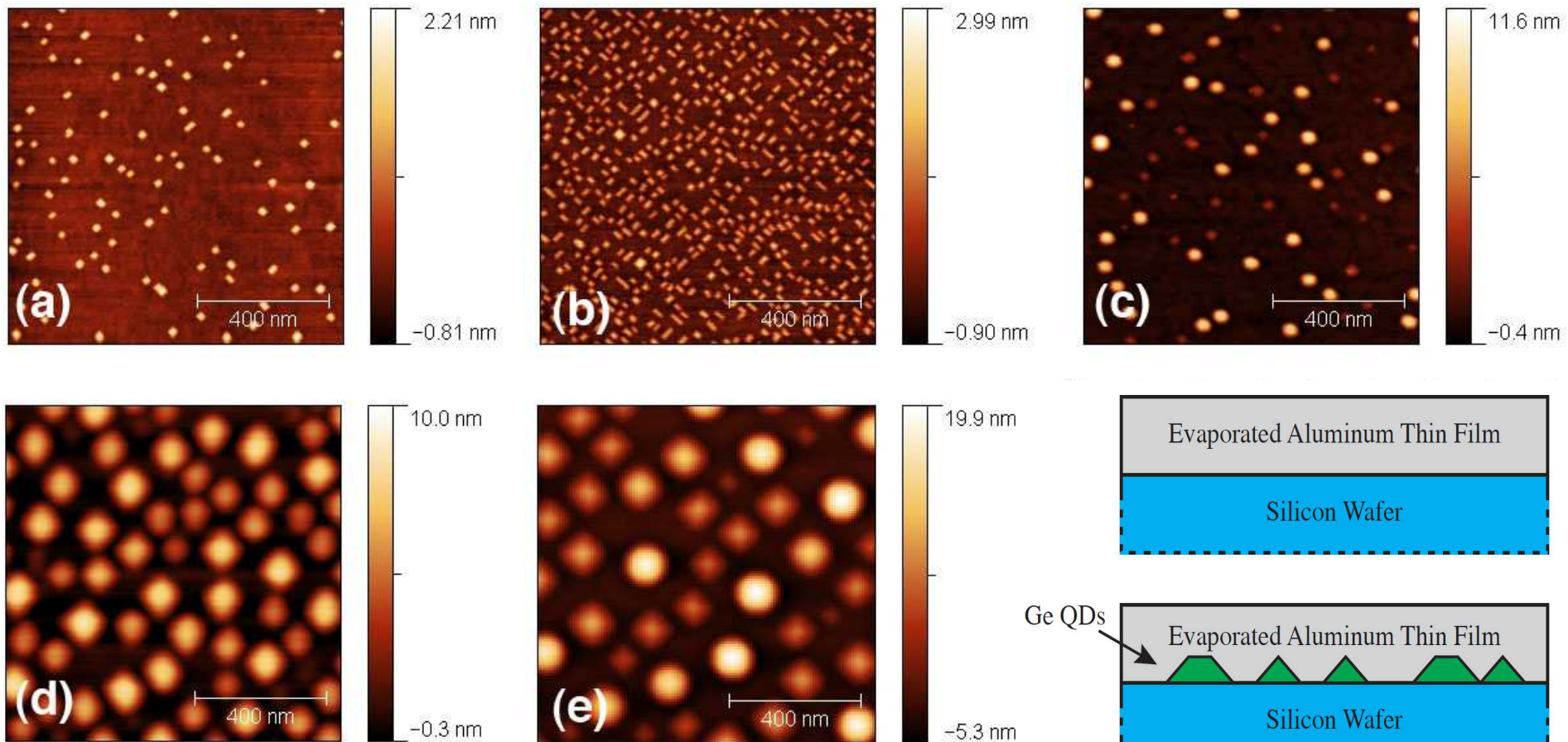




Outline

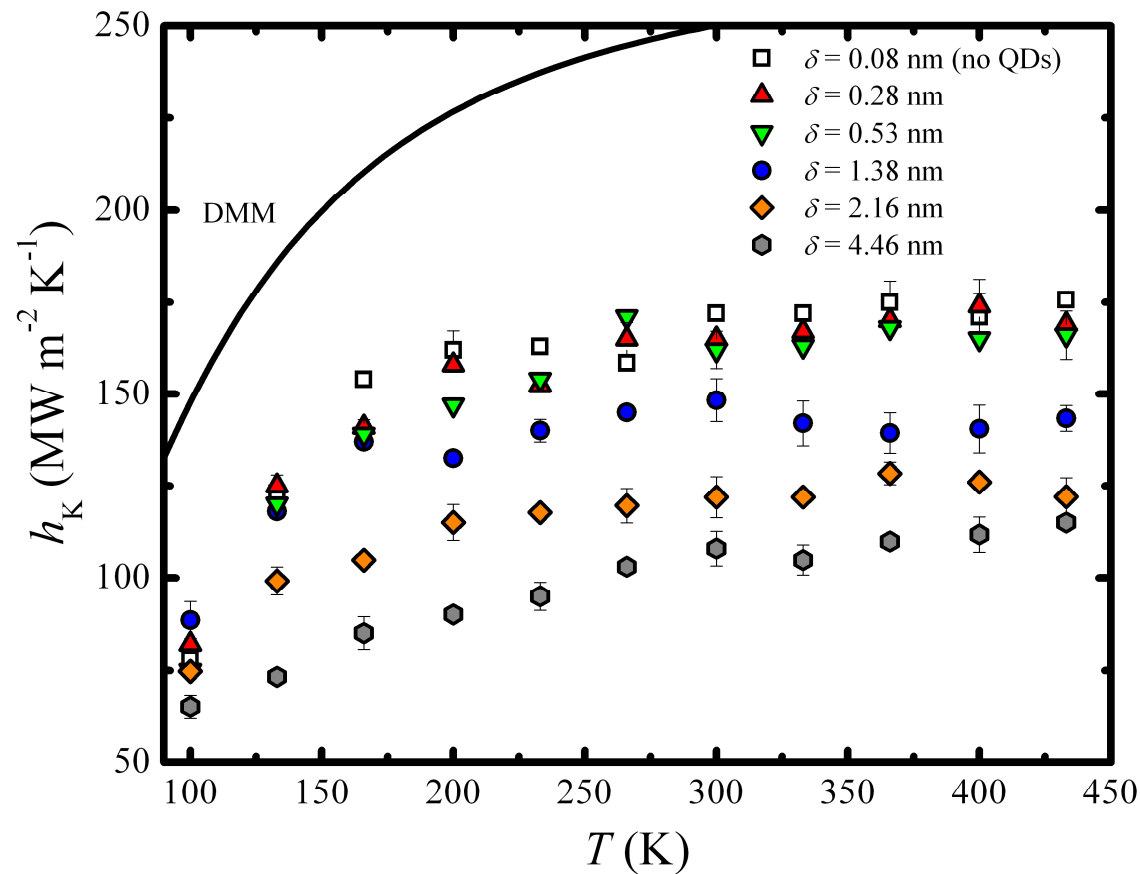
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Using QDs to control interface roughness



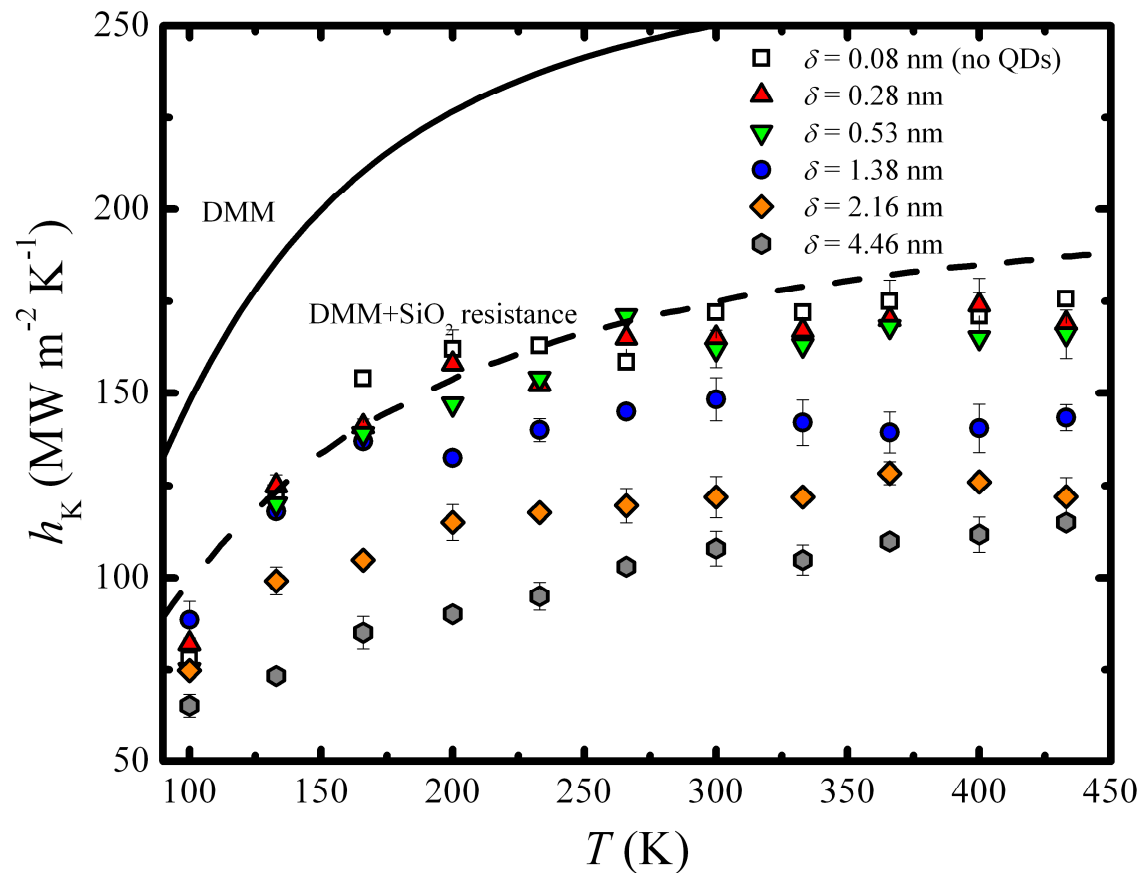
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Thermal boundary conductance of QD patterned interfaces



Thermal boundary conductance of QD patterned interfaces

$$h_{\text{total}} = \left(\frac{1}{h_{\text{DMM}}} + \frac{1}{h_{\text{oxide}}} \right)^{-1} = \left(\frac{1}{h_{\text{DMM}}} + \frac{d_{\text{oxide}}}{\kappa_{\text{SiO}_2}} \right)^{-1}$$





Phonon attenuation

Beer's law for photon attenuation

$$I = I_0 \exp \left[\frac{-4\pi\beta}{\lambda} d \right]$$

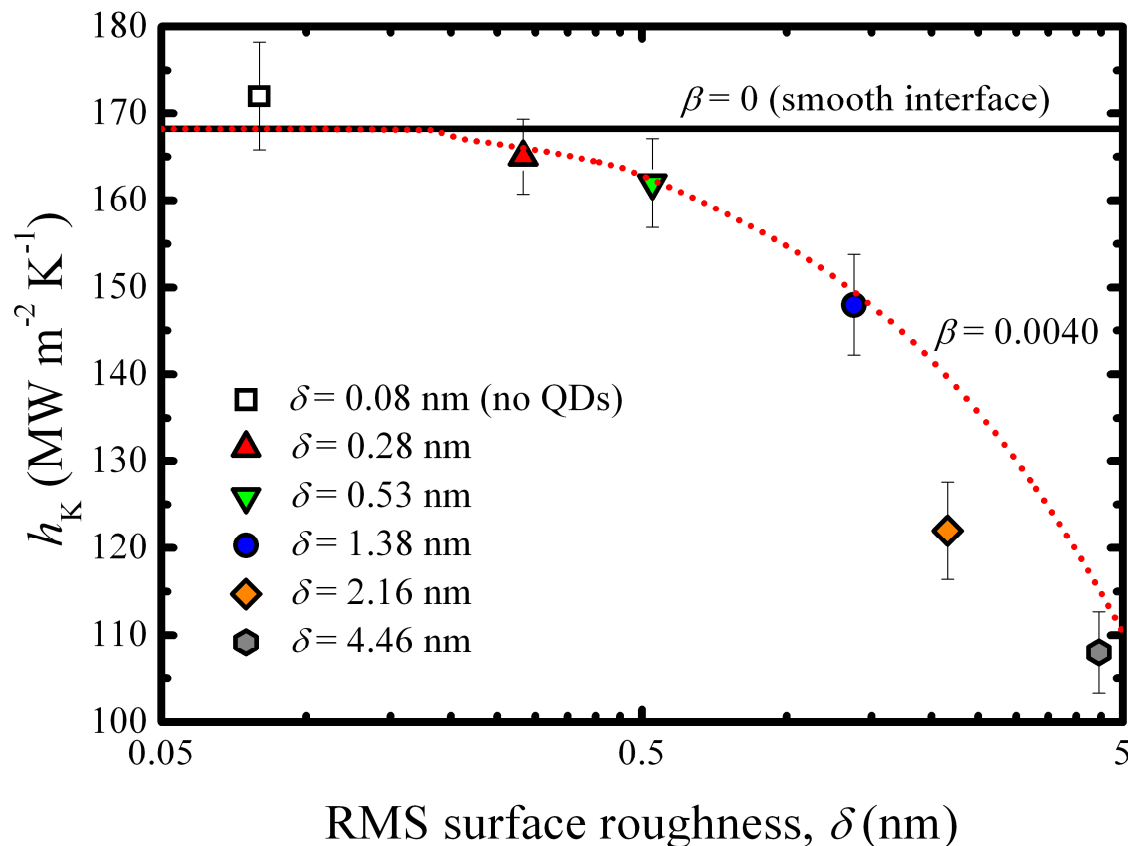
Parallel for phonon attenuation around rough interfaces

$$I = I_0 \exp \left[\frac{-4\pi\beta}{\lambda} \delta \right]$$

Thermal boundary conductance with attenuation

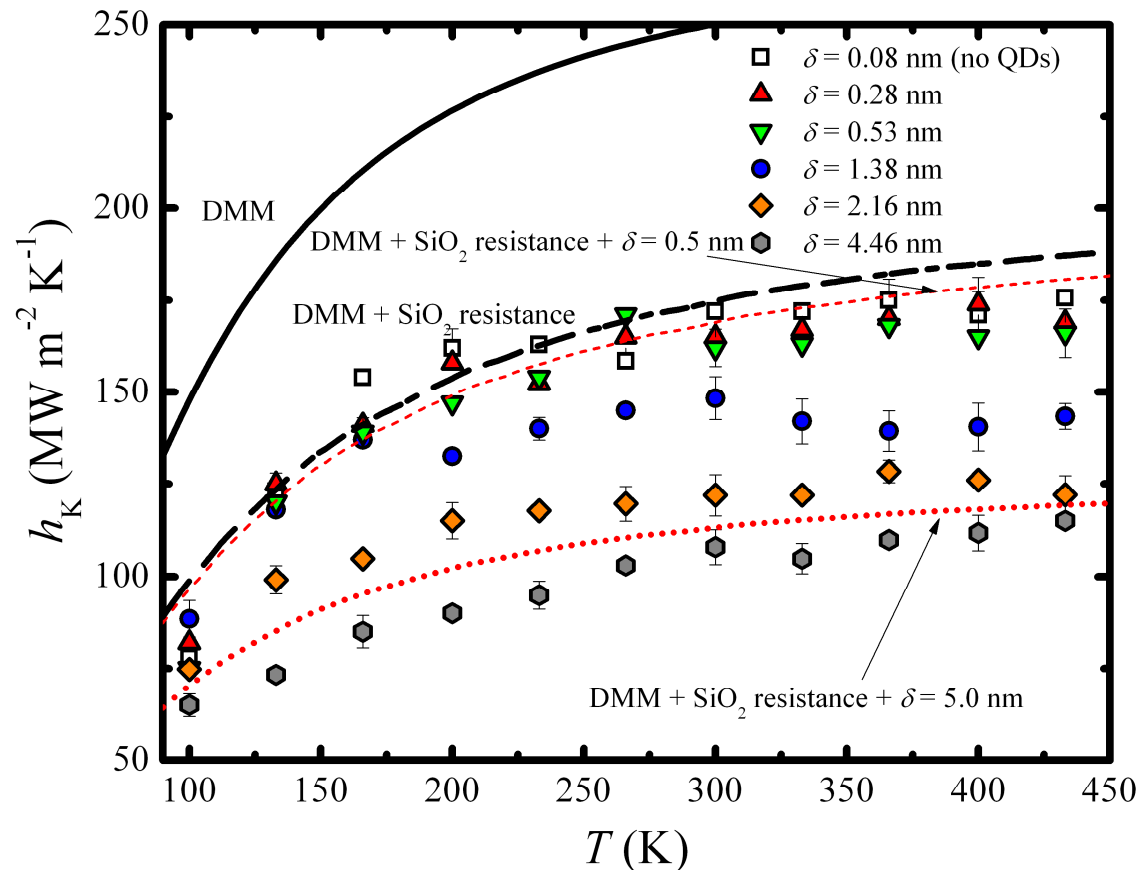
$$h_K = \begin{cases} h_{\text{DMM}} & \lambda > \delta \\ h_{\text{DMM}} \left(\exp \left[- \left(\frac{4\pi\beta}{\lambda} \right) \delta \right] \right) & \lambda < \delta \end{cases}$$

Room temperature trends in thermal boundary conductance at QD patterned interfaces



Long wavelength “phonon filtering” at QD patterned interfaces

$$h_K = \begin{cases} h_{\text{DMM}} & \lambda > \delta \\ h_{\text{DMM}} \left(\exp \left[- \left(\frac{4\pi\beta}{\lambda} \right) \delta \right] \right) & \lambda < \delta \end{cases}$$





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CaTiO₃–SrTiO₃ superlattices on SrTiO₃ substrates

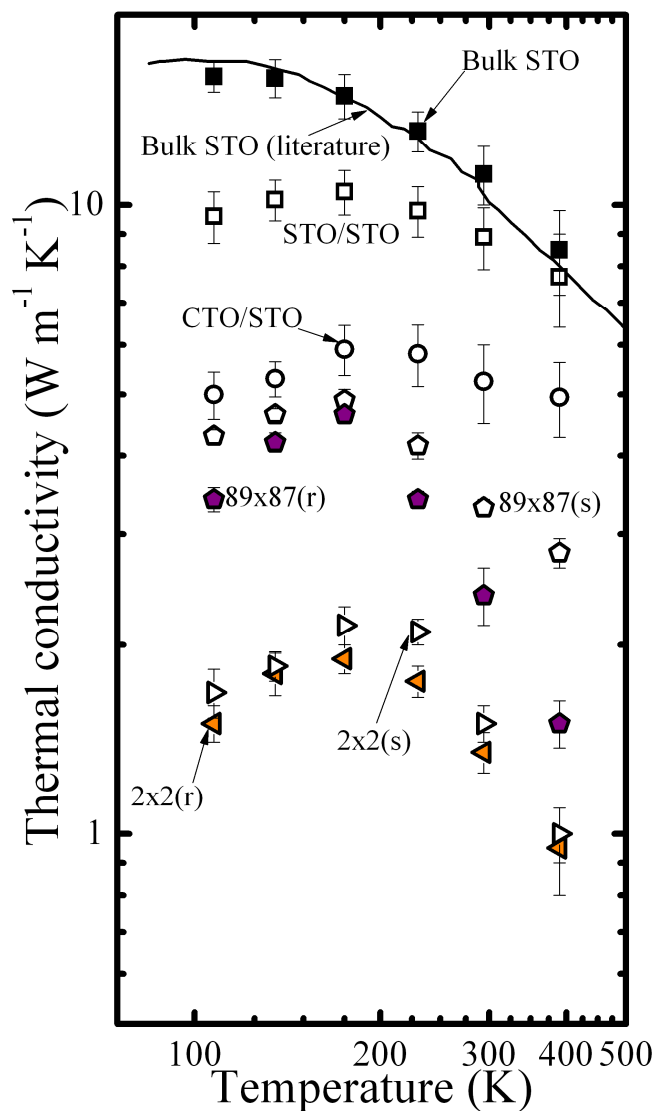
Jayakanth and Pim

Well defined series			
Sample name	desired super lattice CaTiO ₃ + SrTiO ₃ (monolayers)	average doublelayer thickness (nm)	estimated total thickness (nm)
PR281	(4+4) x 65	3.1	205
PR282	(9+9) x 29	7.2	201
PR285	(29+28) x 9	22.6	204
PR286	(89+87) x 3	72.5	217

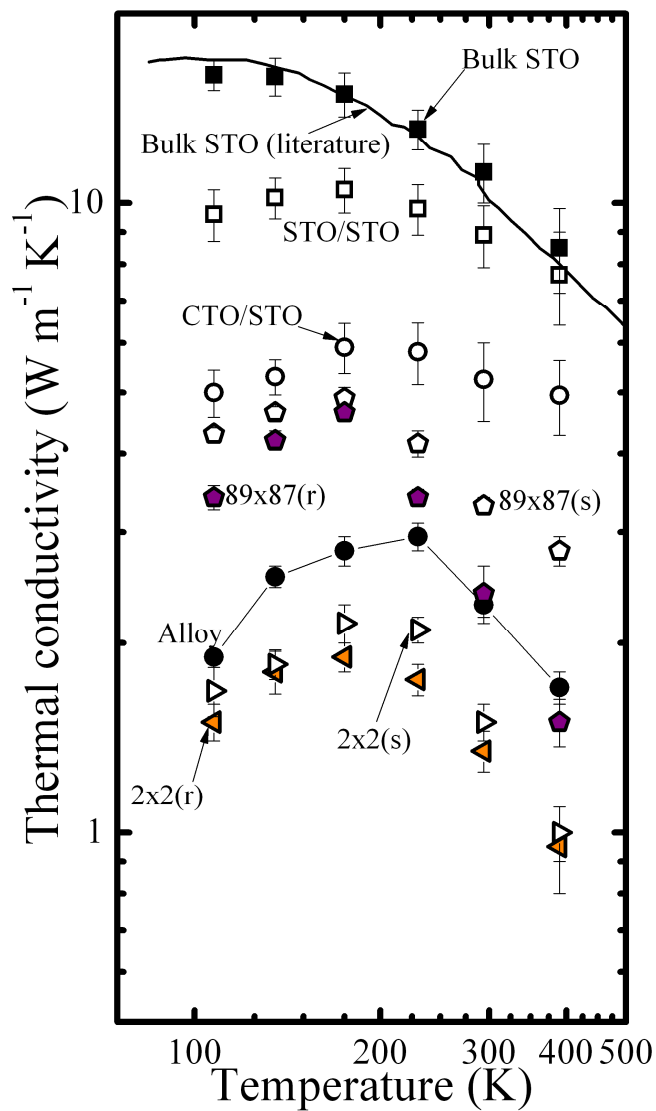
Less defined series			
Sample name	desired super lattice CaTiO ₃ + SrTiO ₃ (monolayers)	average doublelayer thickness (nm)	estimated total thickness (nm)
PR280	(4+4) x 65	3.3	214
110110B	(4+4) x 65	3	195
PR279	(9+9) x 29	7	204
110106	(29+28) x 9	24	216
110104	(89+87) x 3	70	210

Extra samples			
Sample name	desired super lattice CaTiO ₃ + SrTiO ₃ (monolayers)	average doublelayer thickness (nm)	estimated total thickness (nm)
PR316 - Bad*	(2+2) x 130	NA**	150
PR317 - Good	(2+2) x 130	NA**	200
PR318	alloy	NA***	189

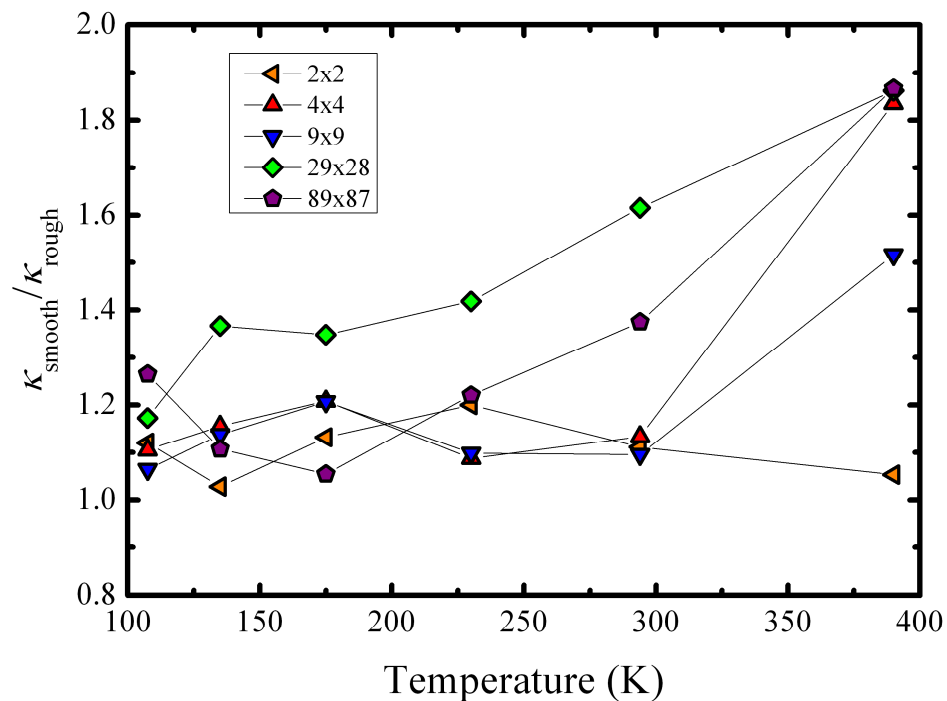
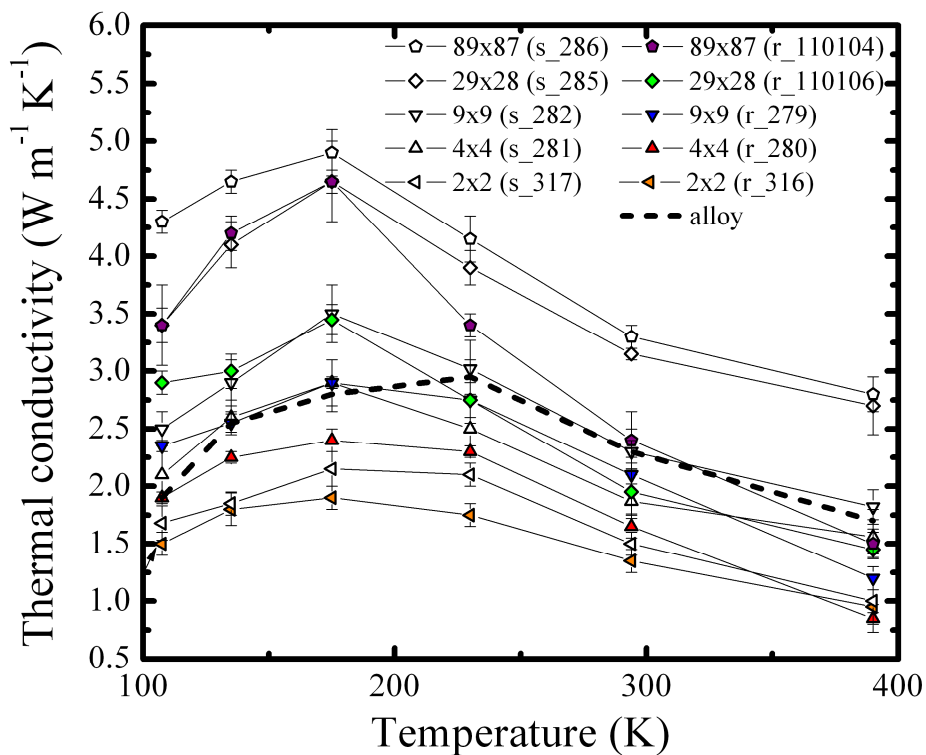
Thermal conductivity of STO/CTO superlattices



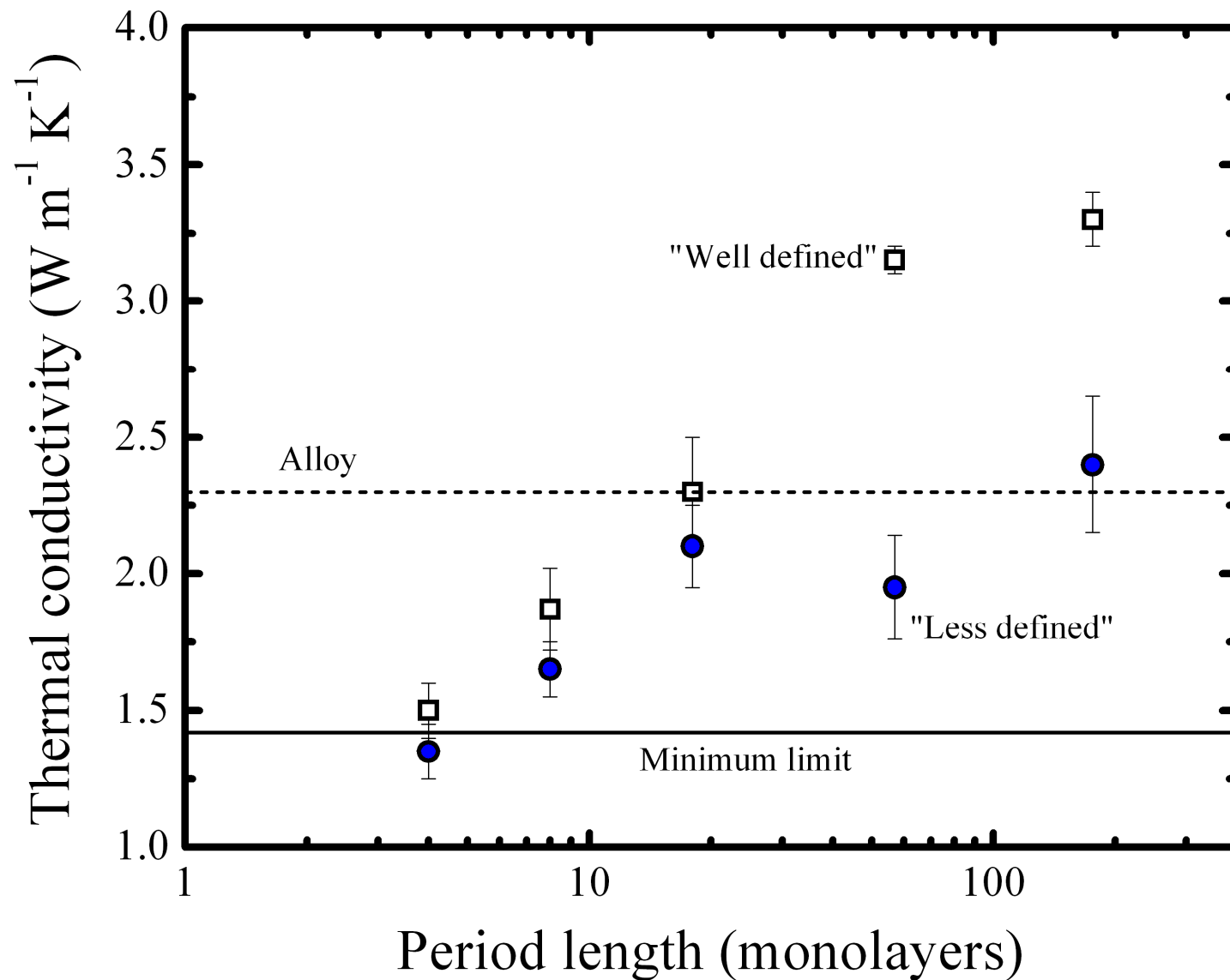
Thermal conductivity of STO/CTO superlattices



Thermal conductivity of STO/CTO superlattices



Approaching the minimum limit



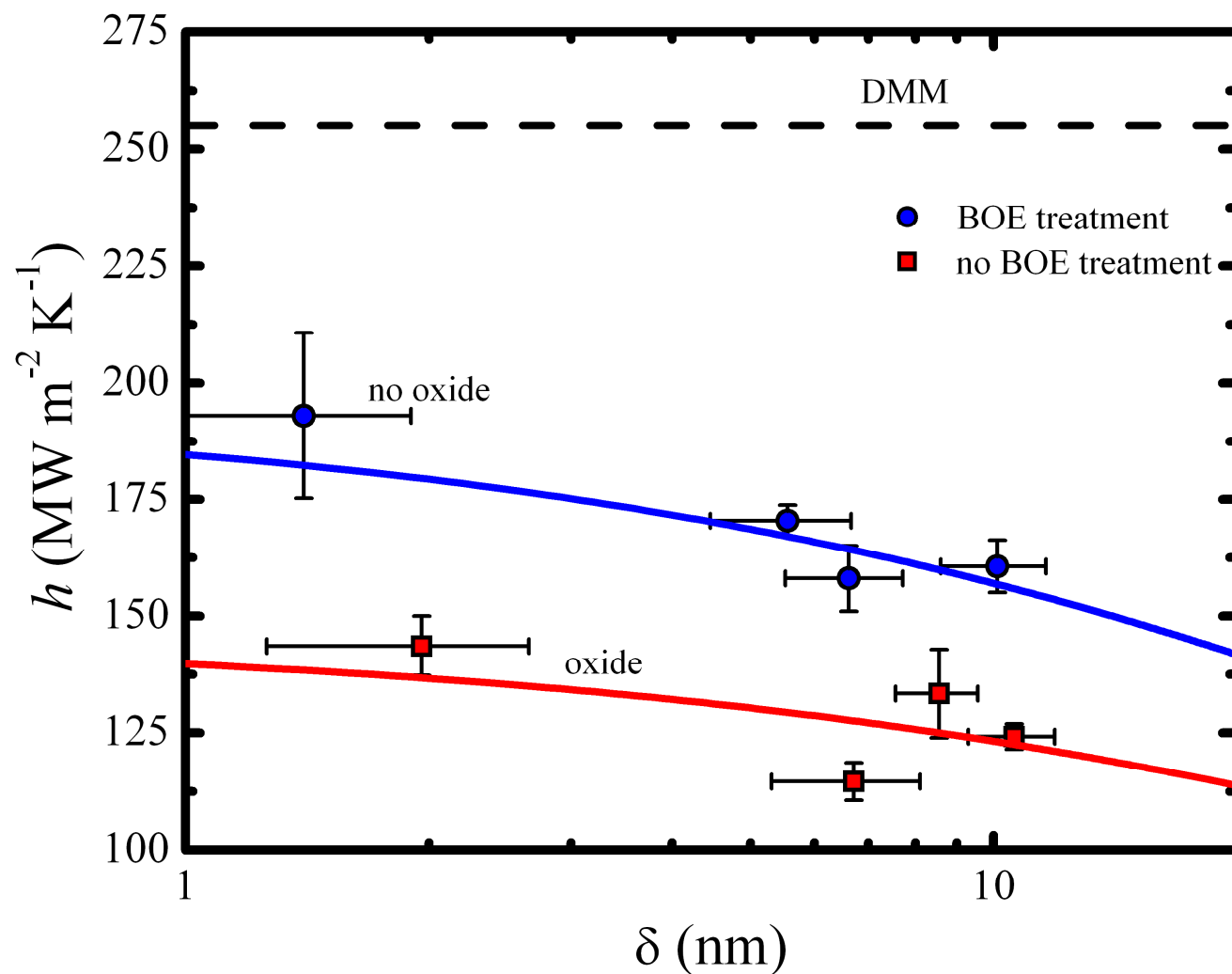
Summary

Controlling thermal boundary conductance with structure: From single interfaces to superlattices

- Thermal resistances at interfaces can pose a dominant resistance in nanosystems
- TDTR is an effective technique to measure thermal resistances in nanosystems
- Quantum dots can be used to control interfacial roughness, and therefore thermal boundary conductance
- Roughening in STO/CTO superlattices can effectively reduce the thermal conductivity (close to theoretical minimum for STO)

Thanks to funding from the Harry S. Truman Fellowship Program through the LDRD office at Sandia.

Chemically roughened Al/Si interfaces



Hopkins *et al.*, *Phys. Rev. B* 82, 085307 (2010)